Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with medium power capability and visible and soldarable side pads.

NPN complement: PBSS4330PAS

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_{C}
- High efficiency due to less heat generation
- High temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) area requirements
- Leadless small SMD plastic package with soldarable side pads
- Exposed heat sink for excellent thermal and electrical conductivity
- Suitable for Automatic Optical Inspection (AOI) of solder joint
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-5	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02; T_{amb} = 25 °C	-	75	107	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	3
2	Е	emitter		1—
3	С	collector	Transparent top view DFN2020D-3 (SOT1061D)	2 sym013

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5330PAS	DFN2020D-3	DFN2020D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061D			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5330PAS	E2

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8. Limiting values

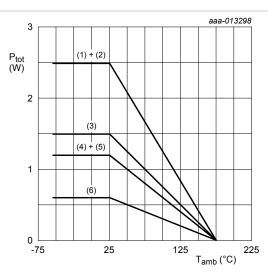
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-30	V
V_{CEO}	collector-emitter voltage	open base		-	-30	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-5	Α
I _B	base current			-	-500	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	600	mW
			[2][3]	-	1.2	W
			[4]	-	1.5	W
			[5][6]	-	2.5	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm².
- [6] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

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- (1) Ceramic PCB, single-sided copper, standard footprint
- (2) FR4 PCB, 4-layer copper, 1 cm²
- (3) FR4 PCB, single-sided copper, 6 cm²
- (4) FR4 PCB, single-sided copper, 1 cm²
- (5) FR4 PCB, 4-layer copper, standard footprint
- (6) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W	
			[2][3]	-	-	125	K/W
	ambient		[4]	-	-	100	K/W
			[5][6]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [6] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm².

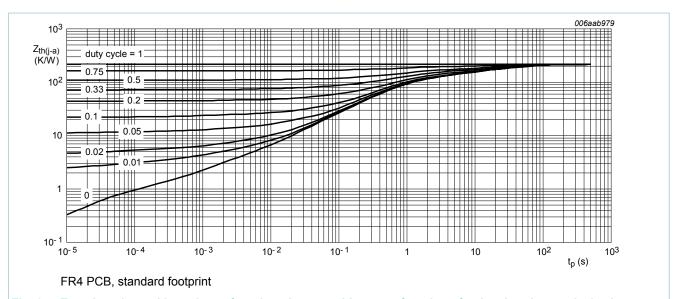


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

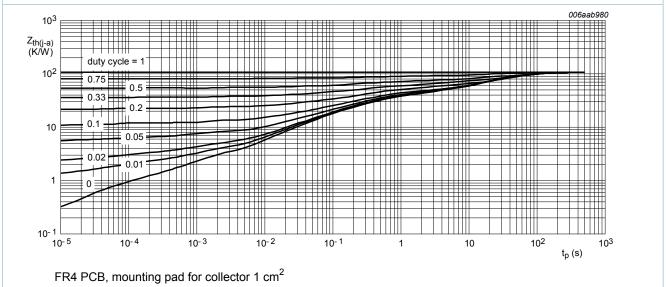


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

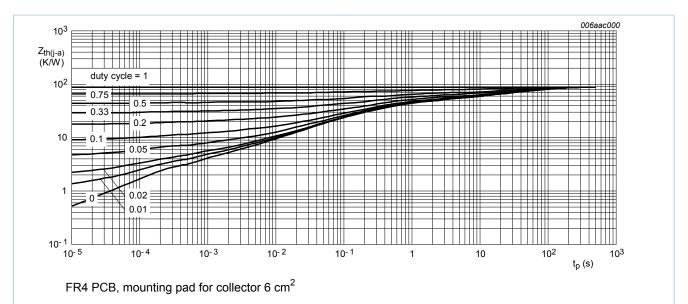


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

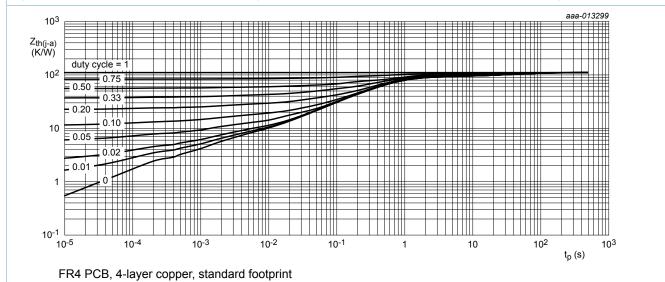


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

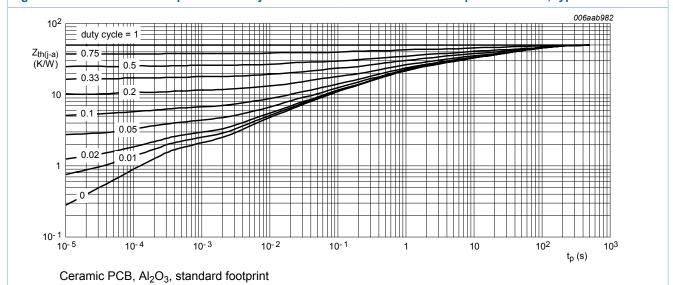


Fig. 7. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

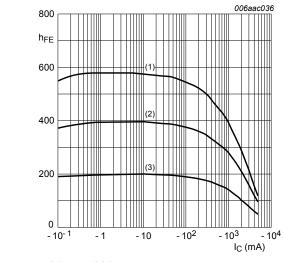
Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -24 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V_{CB} = -24 V; I_{E} = 0 A; T_{j} = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -24 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V; } I_{C} = -0.5 \text{ A; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02; T_{amb} = 25 ^{\circ}\text{C}$	200	320	-	
		V_{CE} = -2 V; I_{C} = -1 A; pulsed; $t_{p} \le 300 \text{ μs}; \delta \le 0.02; T_{amb}$ = 25 °C	175	280	450	
		V_{CE} = -2 V; I_{C} = -2 A; pulsed; $t_{p} \le 300 \text{ μs}; \delta \le 0.02; T_{amb}$ = 25 °C	140	210	-	
		V_{CE} = -2 V; I_{C} = -3 A; pulsed; $t_{p} \le 300 \text{ μs}; \delta \le 0.02; T_{amb}$ = 25 °C	100	160	-	
OLOGI	collector-emitter saturation voltage	I_C = -0.5 A; I_B = -50 mA; pulsed; $t_p \le 300 \text{ μs}; \delta \le 0.02; T_{amb} = 25 \text{ °C}$	-	-45	-70	mV
		I_C = -1 A; I_B = -50 mA; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	-	-90	-130	mV
		I_C = -2 A; I_B = -100 mA; pulsed; $t_p \le 300 \text{ μs}$; $\overline{o} \le 0.02$; T_{amb} = 25 °C	-	-170	-240	mV
		I_C = -3 A; I_B = -300 mA; pulsed;	-	-230	-320	mV
R _{CEsat}	collector-emitter saturation resistance	$t_p \le 300 \text{ μs; } δ \le 0.02; T_{amb} = 25 \text{ °C}$	-	75	107	mΩ
V_{BEsat}	base-emitter saturation voltage	I_C = -2 A; I_B = -100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	-0.89	-1.1	V
		I_C = -3 A; I_B = -300 mA; pulsed; $t_p \le 300 \text{ μs}$; $\overline{o} \le 0.02$; T_{amb} = 25 °C	-	-0.97	-1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -1 A; pulsed; $t_{p} \le 300 \text{ μs}; \delta \le 0.02; T_{amb}$ = 25 °C	-	-0.75	-1	V
t _d	delay time	V_{CC} = -9 V; I_{C} = -2 A; I_{Bon} = -0.1 A;	-	11	-	ns
t _r	rise time	$I_{Boff} = 0.1 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	59	-	ns
t _{on}	turn-on time		-	70	-	ns
t _s	storage time		-	165	-	ns
t _f	fall time		-	35	-	ns
t _{off}	turn-off time		-	200	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	100	165	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	38	45	pF



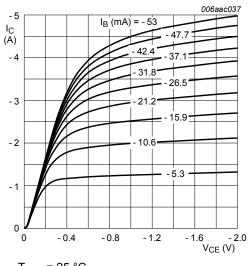
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

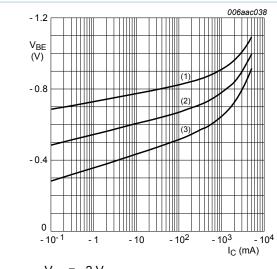
(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 9. Collector current as a function of collectoremitter voltage; typical values



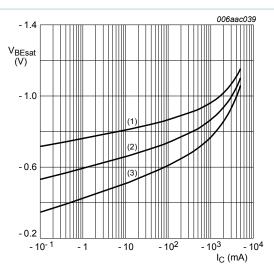
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$





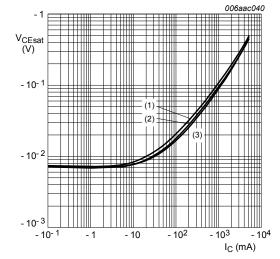
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values



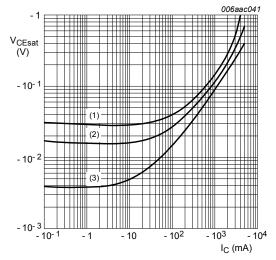
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values

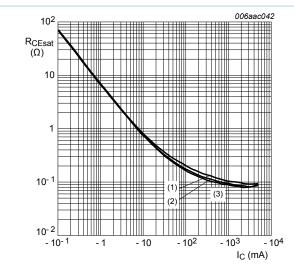


(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values



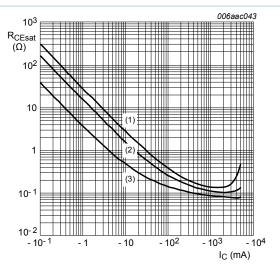
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 100$$

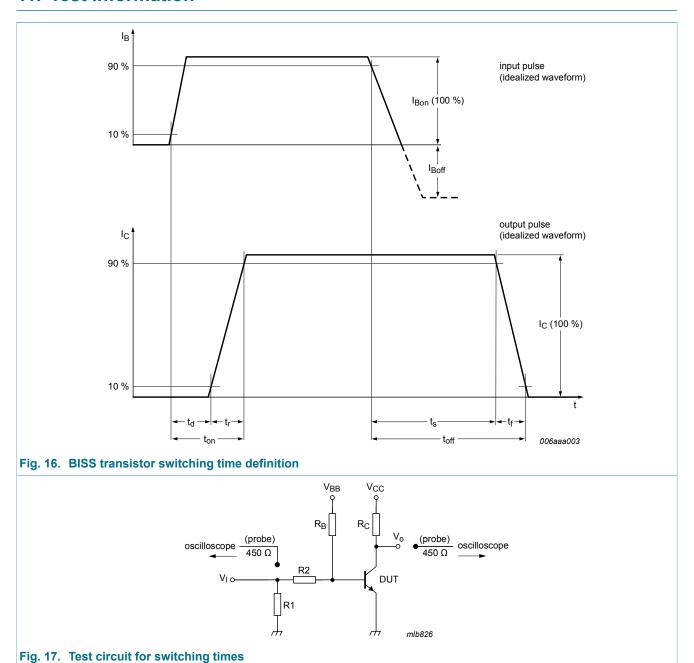
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

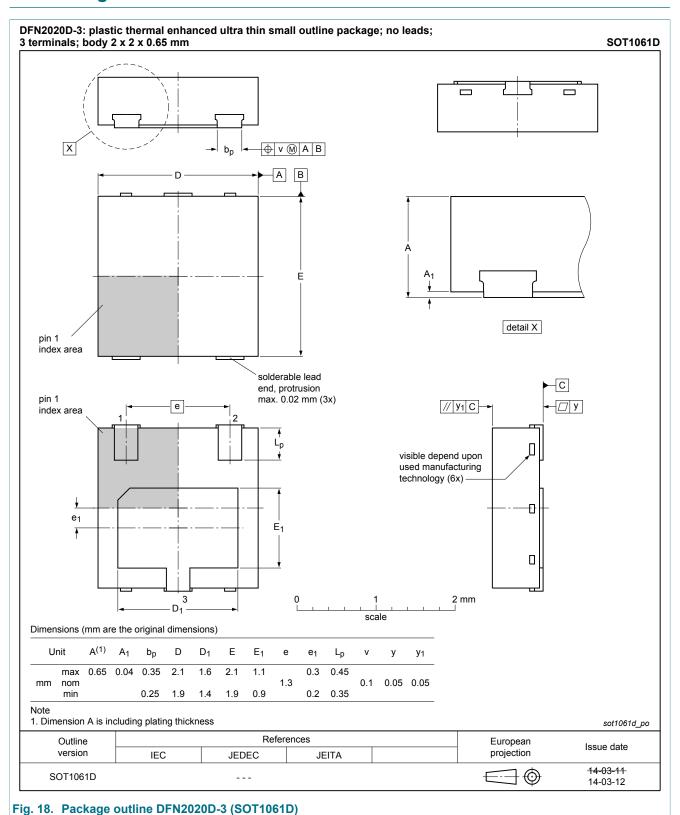


11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



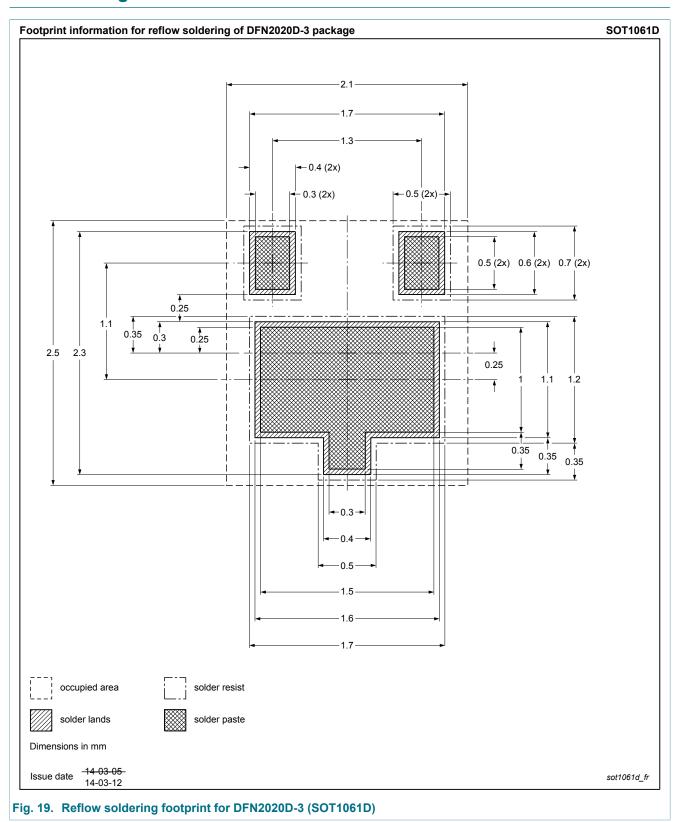
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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5330PAS v.1	20140911	Product data sheet	-	-

30 V, 3 A PNP low VCEsat (BISS) transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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